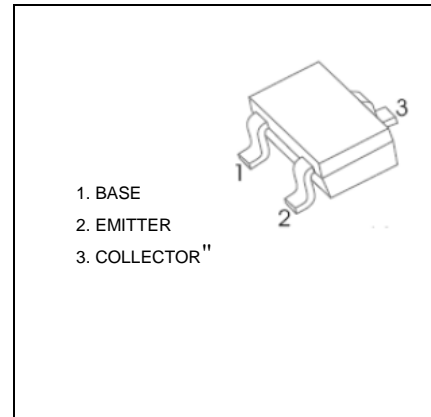


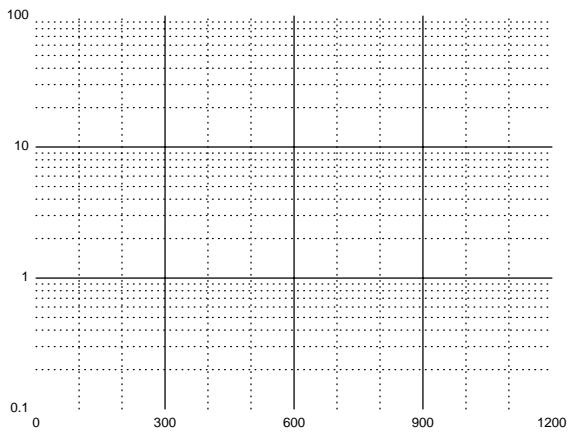
TRANSISTOR (NPN)

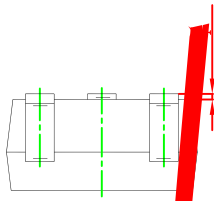
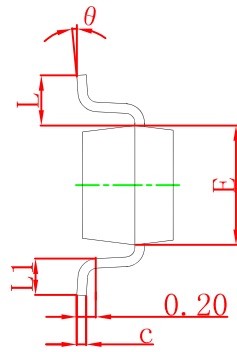
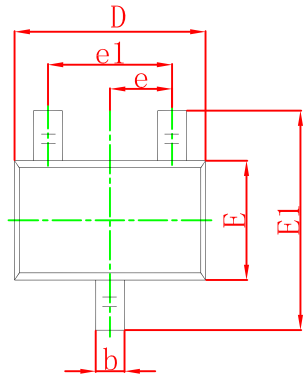
High Breakdown Voltage  
 Low Collector-Emitter Saturation Voltage  
 Complementary to MMSTA92(PNP)



Collector-Base Voltage	300	V	
Collector-Emitter Voltage	300	V	
Emitter-Base Voltage	5	V	
Collector Current -Continuous	0.2	A	
Collector Current -Pulsed	0.5	A	
Collector Power Dissipation	0.3	W	
Thermal Resistance from Junction to Ambient	417	/W	
Junction Temperature	150"		
Storage Temperature	-55-150"		

$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	300				V
$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	300				V
$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5				V
$I_{CBO}$	$V_{CB}=200V, I_E=0$				0.25	$\mu A$
$I_{EBO}$	$V_{EB}=5V, I_C=0$				0.1	$\mu A$
$h_{FE(1)}$	$V_{CE}=10V, I_C=1mA$	60				
	$V_{CE}=10V, I_C=10mA$	100		200		
	$V_{CE}=10V, I_C=30mA$	75				
$V_{CE(sat)}$	$I_C=20mA, I_B=2mA$				0.2	V
$V_{BE(sat)}$	$I_C=20mA, I_B=2mA$				0.9	V
$f_T$	$V_{CE}=20V, I_C=10mA, f=30MHz$	50				MHz





### NOTICE

JCET reserve the right to make modifications,enhancements, improvements, corrections or other changes without further notice to any product herein.JCET does not assume any liability arising out of the application or use of any product described herein.

